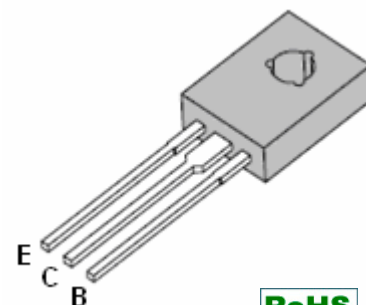


Plastic PNP Epitaxial Silicon Power Transistor

Features

- High collector-emitter breakdown voltage
- Suitable for high voltage general purpose applications
- Complement to MJE340



TO-126

Mechanical Data

Case:	TO-126, Plastic Package
Terminals:	Solderable per MIL-STD-202, Method 208
Weight:	0.08 ounces, 2.24 grams

Absolute Maximum Ratings *(T_{Ambient}=25°C unless noted otherwise)*

Symbol	Description	Value	Unit
V_{CB0}	Collector-Base Voltage	-300	V
V_{CEO}	Collector-Emitter Voltage	-300	V
V_{EBO}	Emitter-Base Voltage	-3	V
I_C	Collector Current Continuous	-0.5	A
P_D	Power Dissipation @ T _a =25°C	1.25	W
	Derate above 25°C	10	mW/°C
P_D	Power Dissipation @ T _c =25°C	20	W
	Derate above 25°C	0.16	W/°C
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-65 ~ +150	°C

Plastic PNP Epitaxial Silicon Power Transistor

MJE350

Thermal Characteristics

Symbol	Description	Value	Unit
RθJA	Thermal Resistance from Junction to Ambient in Free Air	100	$^{\circ}\text{C}/\text{W}$
RθJC	Thermal Resistance from Junction to Case	6.25	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics ($T_{\text{Ambient}}=25^{\circ}\text{C}$ unless noted otherwise)

Symbol	Description	Conditions	Min.	Max.	Unit
V$_{\text{CEO(sus)}}$	Collector-Emitter Sustaining Voltage	$I_{\text{C}}=-1\text{mA}$, $I_{\text{B}}=0$	-300	-	V
I$_{\text{CBO}}$	Collector-Base Cut-off Current	$V_{\text{CB}}=-300\text{V}$, $I_{\text{E}}=0$	-	-100	μA
I$_{\text{EBO}}$	Emitter-Base Cut-off Current	$V_{\text{EB}}=-3\text{V}$, $I_{\text{C}}=0$	-	-100	μA
h$_{\text{FE}}$	DC Current Gain	$V_{\text{CE}}=-10\text{V}$, $I_{\text{C}}=-50\text{mA}$	30	240	

Typical Characteristics Curves

Fig.1- DC Current Gain

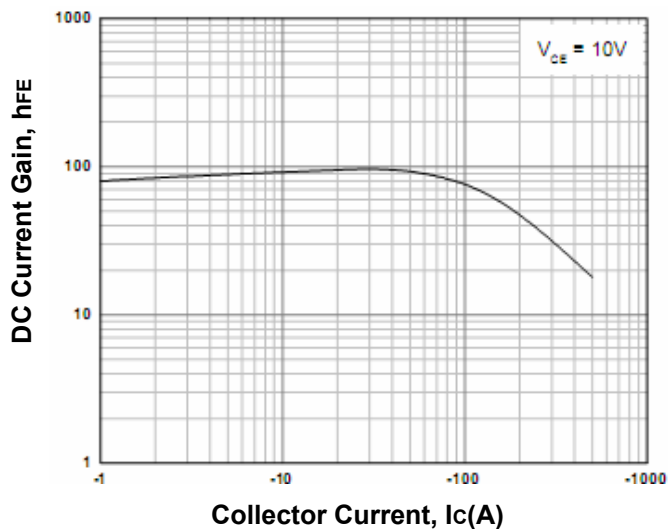
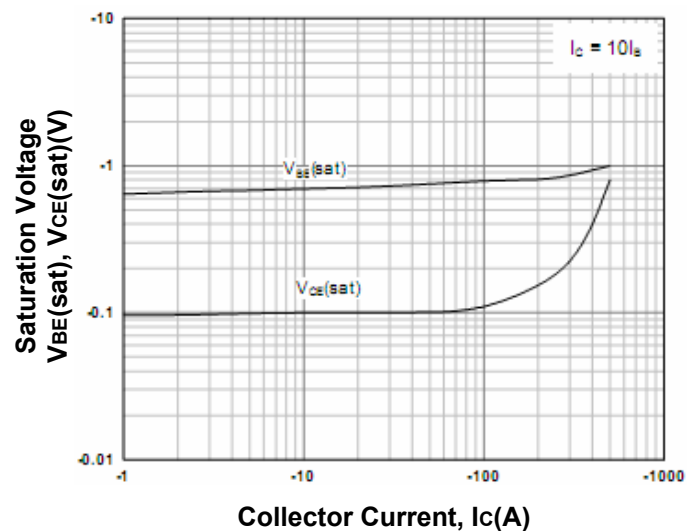


Fig.2- Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Plastic PNP Epitaxial Silicon Power Transistor

MJE350

Fig.3- Safe Operating Area

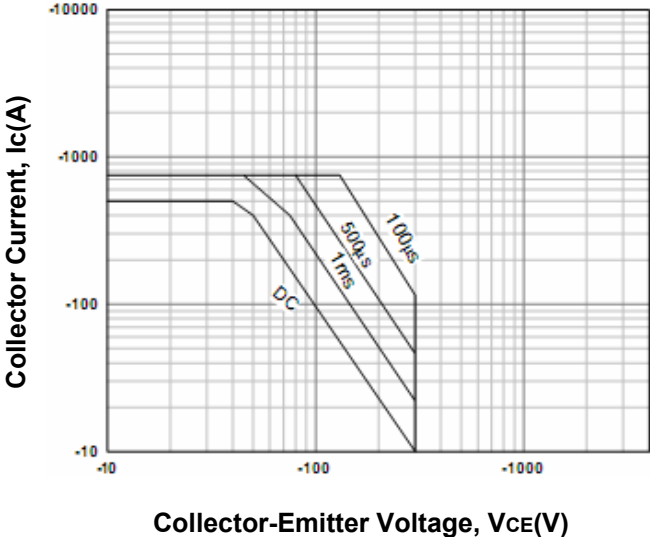
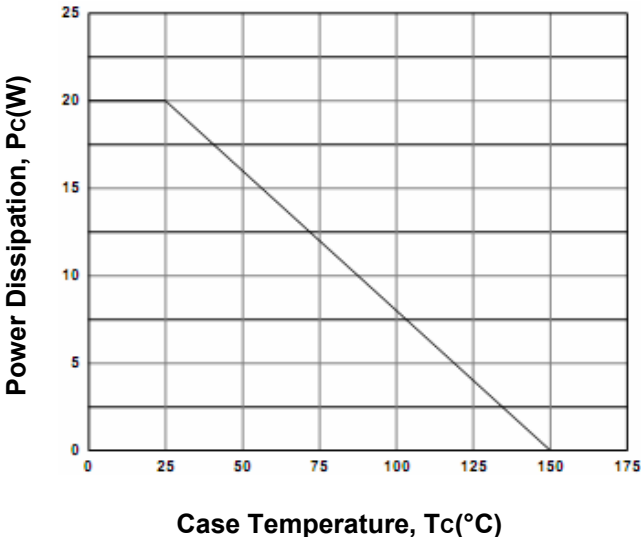
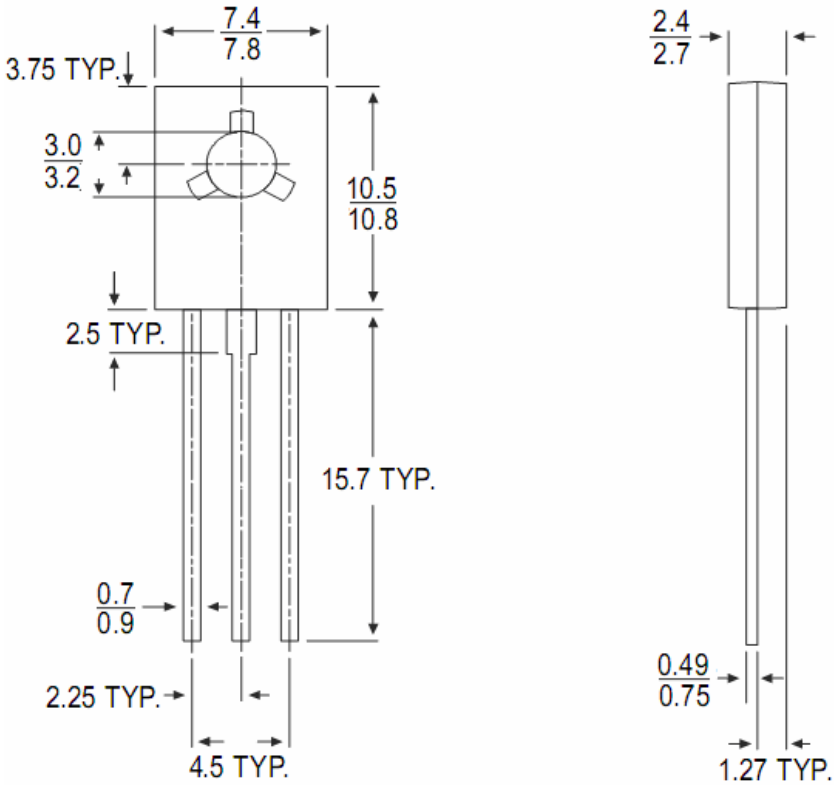


Fig.4- Power Derating



Dimensions in mm



TO-126

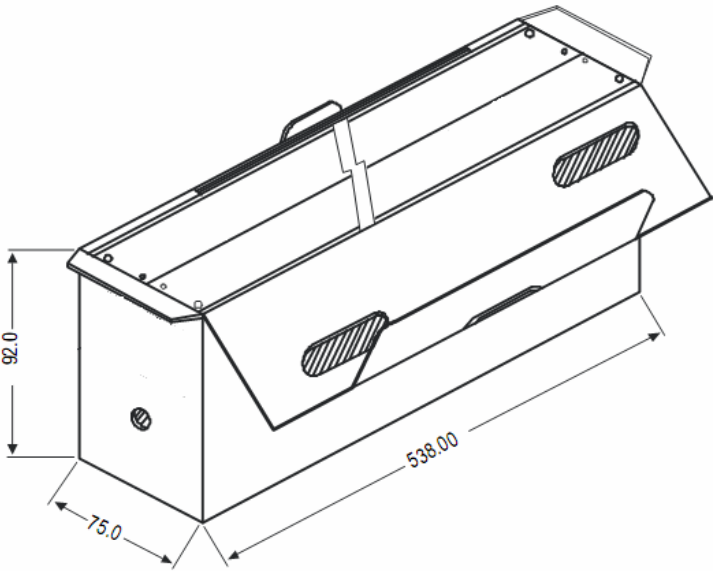
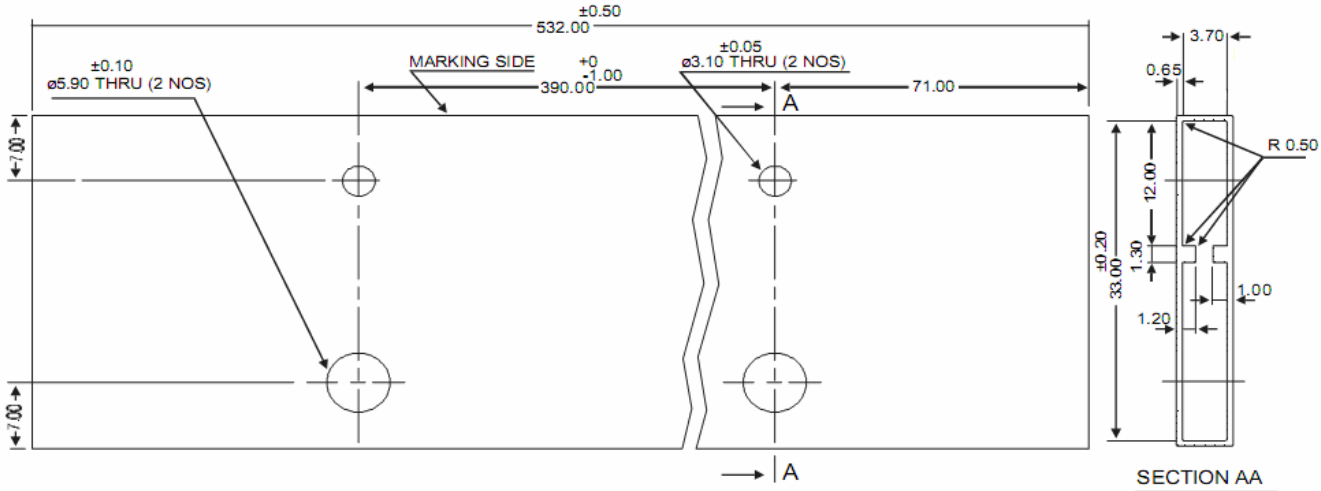


Plastic PNP Epitaxial Silicon Power Transistor

MJE350

Packing Information

Tube Dimensions



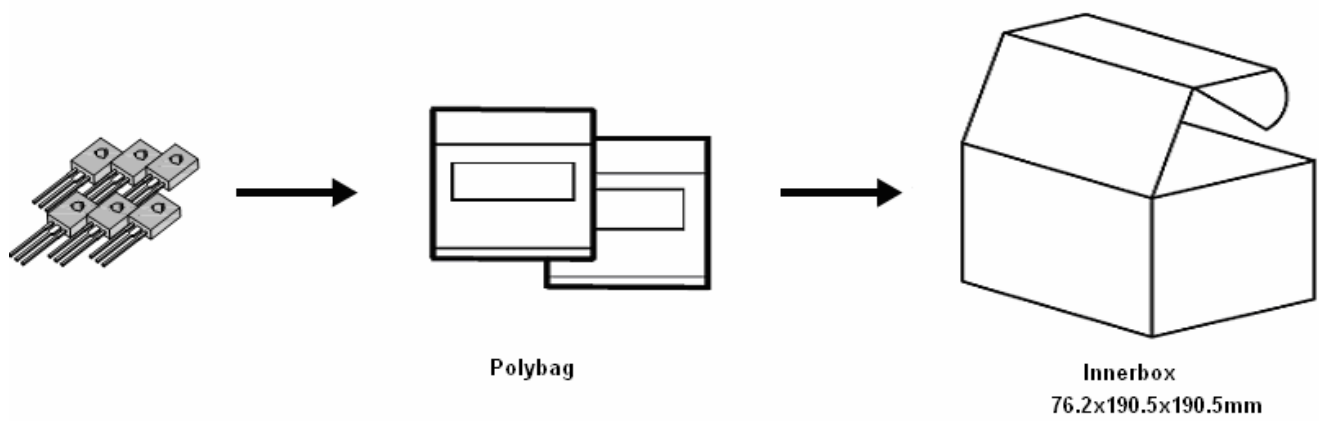
GENERAL TOLERANCE					
0 mm	0.01 mm	30.01 mm	120.01 mm	ABOVE	ANGULAR
5 mm	30 mm	120 mm	315 mm	315 mm	
±0.1	±0.2	±0.3	±0.5	±0.8	±0° 30'

All dimensions in mm

Plastic PNP Epitaxial Silicon Power Transistor

MJE350

Bulk Dimensions



Packing Details

Pack	Description	Standard Pack	Inner Box	Carton Box
BL	Bulk, RoHS	500/polybag	2K	32K
TU	Tube, RoHS	50/tube	1K	10K

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